distribution of surface concentration. The position and the length of this zone is controlled by the reaction rate between BBr_3 and O_2. This rate is enhanced by increasing the concentration of reactants or the temperature of reaction. This is observed to cause earlier formation of B_2O_3 in the furnace tube and results in a shift in the position of the zone of uniform sheet resistance towards the gas inlet of the tube. To a lesser extent the uniformity of diffusion is also affected by total N_2 carrier gas velocity and the spacing of wafers.

A nonuniform diffusion degrades the electrical parameters of a device due essentially to variation in surface concentration and concentration profile in the base region.

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Correction

Arctic Ice Type Identification by Radar

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On page 610 of the above paper,[1] Table I should have read as follows:

TABLE I
SURFACE ROUGHNESS FACTOR

Ice Type	S
Multiyear Ice	
Line 92 (A)	9.2
Line 92 (C)	20.2
Line 94	17.9
First-Year Ice	
Line 91	70.7
Line 92	52.3
Line 94	84.6
Smooth First-Year Ice	
Line 91	119.5
Open Water	
Line 91	546.9
Pressure Ridge	
Line 94	16.2

Fig. 9, on the same page, should have agreed with this revised table.

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[1] J. W. Rouse, Jr., *Proc. IEEE*, vol. 57, pp. 605–611, April 1969.